



(51) International Patent Classification:

H01L 29/786 (2006.01) *H01L 21/8244* (2006.01)
G02F 1/1368 (2006.01) *H01L 27/105* (2006.01)
H01L 21/336 (2006.01) *H01L 27/108* (2006.01)
H01L 21/8242 (2006.01) *H01L 27/11* (2006.01)

(21) International Application Number:

PCT/JP2012/083764

(22) International Filing Date:

19 December 2012 (19.12.2012)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2011-282509 23 December 2011 (23.12.2011) JP

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: SEMICONDUCTOR DEVICE

(57) Abstract: Provided is a transistor which includes an oxide semiconductor film and has stable electrical characteristics. In the transistor, over an oxide film which can release oxygen by being heated, a first oxide semiconductor film which can suppress oxygen release at least from the oxide film is formed. Over the first oxide semiconductor film, a second oxide semiconductor film is formed. With such a structure in which the oxide semiconductor films are stacked, the oxygen release from the oxide film can be suppressed at the time of the formation of the second oxide semiconductor film, and oxygen can be released from the oxide film in later-performed heat treatment. Thus, oxygen can pass through the first oxide semiconductor film to be favorably supplied to the second oxide semiconductor film. Oxygen supplied to the second oxide semiconductor film can suppress the generation of oxygen deficiency, resulting in stable electrical characteristics.

